

# Weimin M Chen

## List of Publications by Citations

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435  
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468  
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8,466  
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5.48  
L-index

#	Paper	IF	Citations
435	Semi-metallic polymers. <i>Nature Materials</i> , <b>2014</b> , 13, 190-4	27	605
434	Design rules for minimizing voltage losses in high-efficiency organic solar cells. <i>Nature Materials</i> , <b>2018</b> , 17, 703-709	27	500
433	Mechanism for low-temperature photoluminescence in GaNAs/GaAs structures grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 501-503	3.4	227
432	Silicon vacancy related defect in 4H and 6H SiC. <i>Physical Review B</i> , <b>2000</b> , 61, 2613-2620	3.3	202
431	Electronic Properties of Ga(In)NAs Alloys. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , <b>2001</b> , 6, 1		157
430	Direct determination of electron effective mass in GaNAs/GaAs quantum wells. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 1843	3.4	156
429	. <i>IEEE Transactions on Electron Devices</i> , <b>2007</b> , 54, 1040-1048	2.9	121
428	Mechanism responsible for the semi-insulating properties of low-temperature-grown GaAs. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 3002-3004	3.4	116
427	Oxygen and zinc vacancies in as-grown ZnO single crystals. <i>Journal Physics D: Applied Physics</i> , <b>2009</b> , 42, 175411	3	106
426	Wide bandgap GaN-based semiconductors for spintronics. <i>Journal of Physics Condensed Matter</i> , <b>2004</b> , 16, R209-R245	1.8	106
425	Electron effective masses in 4H SiC. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 1074-1076	3.4	89
424	Mechanism for rapid thermal annealing improvements in undoped GaN <sub>x</sub> As <sub>1-x</sub> /GaAs structures grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 2325-2327	3.4	87
423	Influence of conduction-band nonparabolicity on electron confinement and effective mass in GaN <sub>x</sub> As <sub>1-x</sub> /GaAs quantum wells. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	85
422	Ferromagnetism in Transition-Metal Doped ZnO. <i>Journal of Electronic Materials</i> , <b>2007</b> , 36, 462-471	1.9	80
421	Room-temperature defect-engineered spin filter based on a non-magnetic semiconductor. <i>Nature Materials</i> , <b>2009</b> , 8, 198-202	27	78
420	Time-resolved studies of photoluminescence in GaN <sub>x</sub> P <sub>1-x</sub> alloys: Evidence for indirect-direct band gap crossover. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 52-54	3.4	77
419	Band gap properties of Zn <sub>1-x</sub> Cd <sub>x</sub> O alloys grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 151909	3.4	71

418	Electronic structure of the neutral silicon vacancy in 4H and 6H SiC. <i>Physical Review B</i> , <b>2000</b> , 62, 16555-16560	15.6	65
417	Electron effective masses and mobilities in high-purity 6H SiC chemical vapor deposition layers. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 3209-3211	3.4	65
416	Trap-Assisted Recombination via Integer Charge Transfer States in Organic Bulk Heterojunction Photovoltaics. <i>Advanced Functional Materials</i> , <b>2014</b> , 24, 6309-6316	15.6	60
415	Determination of the electron effective-mass tensor in 4H SiC. <i>Physical Review B</i> , <b>1996</b> , 53, 15409-15412	3.3	60
414	Formation of nonradiative defects in molecular beam epitaxial GaN <sub>x</sub> As <sub>1-x</sub> studied by optically detected magnetic resonance. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 3089-3091	3.4	59
413	Radiative recombination mechanism in GaN <sub>x</sub> P <sub>1-x</sub> alloys. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 1740-1742	3.4	59
412	A Free-Standing High-Output Power Density Thermoelectric Device Based on Structure-Ordered PEDOT:PSS. <i>Advanced Electronic Materials</i> , <b>2018</b> , 4, 1700496	6.4	58
411	Phosphorus antisite defects in low-temperature InP. <i>Physical Review B</i> , <b>1993</b> , 47, 4111-4114	3.3	57
410	Ground-state electron transfer in all-polymer donor-acceptor heterojunctions. <i>Nature Materials</i> , <b>2020</b> , 19, 738-744	27	56
409	Photoluminescence of GaN: Effect of electron irradiation. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 2968-2970	3.4	55
408	Effect of growth temperature on photoluminescence of GaNAs/GaAs quantum well structures. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 3781-3783	3.4	55
407	Dominant recombination centers in Ga(In)NAs alloys: Ga interstitials. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 241904	3.4	54
406	Nitrogen passivation induced by atomic hydrogen: The GaP <sub>1-x</sub> N <sub>x</sub> case. <i>Physical Review B</i> , <b>2003</b> , 67,	3.3	51
405	Applications of optically detected magnetic resonance in semiconductor layered structures. <i>Thin Solid Films</i> , <b>2000</b> , 364, 45-52	2.2	51
404	Signature of an intrinsic point defect in GaN <sub>x</sub> As <sub>1-x</sub> . <i>Physical Review B</i> , <b>2001</b> , 63,	3.3	50
403	Type I band alignment in the GaN <sub>x</sub> As <sub>1-x</sub> /GaAs quantum wells. <i>Physical Review B</i> , <b>2000</b> , 63,	3.3	50
402	A high-conductivity n-type polymeric ink for printed electronics. <i>Nature Communications</i> , <b>2021</b> , 12, 2354	17.4	49
401	Optical detection of cyclotron resonance for characterization of recombination processes in semiconductors. <i>Critical Reviews in Solid State and Materials Sciences</i> , <b>1994</b> , 19, 241-301	10.1	47

400	Analysis of band anticrossing in GaN <sub>x</sub> P <sub>1-x</sub> alloys. <i>Physical Review B</i> , <b>2004</b> , 70,	3-3	46
399	Zinc-Vacancy Donor Complex: A Crucial Compensating Acceptor in ZnO. <i>Physical Review Applied</i> , <b>2014</b> , 2,	4-3	45
398	Hydrogen-induced improvements in optical quality of GaNAs alloys. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 3662-3664	3-4	45
397	High quality 4H-SiC epitaxial layers grown by chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 1373-1375	3-4	45
396	Recombination processes in N-containing III-V ternary alloys. <i>Solid-State Electronics</i> , <b>2003</b> , 47, 467-475	1-7	39
395	Ligand hyperfine interaction at the neutral silicon vacancy in 4H- and 6H-BiC. <i>Physical Review B</i> , <b>2002</b> , 66,	3-3	39
394	Magneto-optical and light-emission properties of III-As-N semiconductors. <i>Semiconductor Science and Technology</i> , <b>2002</b> , 17, 815-822	1-8	39
393	Direct observation of intercenter charge transfer in dominant nonradiative recombination channels in silicon. <i>Physical Review Letters</i> , <b>1991</b> , 67, 1914-1917	7-4	39
392	Observation of rapid direct charge transfer between deep defects in silicon. <i>Physical Review Letters</i> , <b>1994</b> , 72, 2939-2942	7-4	37
391	Dilute Nitride Nanowire Lasers Based on a GaAs/GaNAs Core/Shell Structure. <i>Nano Letters</i> , <b>2017</b> , 17, 1775-1781	11.5	36
390	Er/O and Er/F doping during molecular beam epitaxial growth of Si layers for efficient 1.54 $\mu$ m light emission. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 3383-3385	3-4	36
389	Properties of Ga-interstitial defects in Al <sub>x</sub> Ga <sub>1-x</sub> NyP <sub>1-y</sub> . <i>Physical Review B</i> , <b>2005</b> , 71,	3-3	36
388	Hole effective masses in 4H SiC. <i>Physical Review B</i> , <b>2000</b> , 61, R10544-R10546	3-3	36
387	On the origin of spin loss in GaMnN/InGaN light-emitting diodes. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 2599-2601	3-4	35
386	Optically detected magnetic resonance studies of defects in electron-irradiated 3C SiC layers. <i>Physical Review B</i> , <b>1997</b> , 55, 2863-2866	3-3	33
385	Turning ZnO into an Efficient Energy Upconversion Material by Defect Engineering. <i>Advanced Functional Materials</i> , <b>2014</b> , 24, 3760-3764	15.6	32
384	Microscopic identification and electronic structure of a di-hydrogen-vacancy complex in silicon by optical detection of magnetic resonance. <i>Physical Review Letters</i> , <b>1990</b> , 64, 3042-3045	7-4	32
383	Effect of Backbone Regiochemistry on Conductivity, Charge Density, and Polaron Structure of n-Doped Donor-Acceptor Polymers. <i>Chemistry of Materials</i> , <b>2019</b> , 31, 3395-3406	9.6	31

382	Defects in N, O and N, Zn implanted ZnO bulk crystals. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 103509	2.5	31
381	Exciton spin relaxation in diluted magnetic semiconductor Zn <sub>1-x</sub> MnxSe/CdSe superlattices: Effect of spin splitting and role of longitudinal optical phonons. <i>Physical Review B</i> , <b>2003</b> , 67,	3.3	31
380	Temperature dependence of the GaN <sub>x</sub> P <sub>1-x</sub> band gap and effect of band crossover. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 3984-3986	3.4	31
379	Photoluminescence and Zeeman effect in chromium-doped 4H and 6H SiC. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 4348-4353	2.5	31
378	Evidence for coupling between exciton emissions and surface plasmon in Ni-coated ZnO nanowires. <i>Nanotechnology</i> , <b>2012</b> , 23, 425201	3.4	30
377	Growth and characterization of dilute nitride GaN <sub>x</sub> P <sub>1-x</sub> nanowires and GaN <sub>x</sub> P <sub>1-x</sub> /GaNyP <sub>1-y</sub> core/shell nanowires on Si (111) by gas source molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 072107	3.4	29
376	Efficient room-temperature nuclear spin hyperpolarization of a defect atom in a semiconductor. <i>Nature Communications</i> , <b>2013</b> , 4, 1751	17.4	29
375	Tunable laser spectroscopy of spin injection in ZnMnSe/ZnCdSe quantum structures. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 2196-2198	3.4	29
374	Electronic structure of bound excitons in semiconductors. <i>Physica B: Physics of Condensed Matter &amp; C: Atomic, Molecular and Plasma Physics, Optics</i> , <b>1987</b> , 146, 256-285		29
373	Carbon-vacancy related defects in 4H- and 6H-SiC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 61-62, 202-206	3.1	28
372	Optically detected magnetic resonance studies of intrinsic defects in 6H-SiC. <i>Semiconductor Science and Technology</i> , <b>1999</b> , 14, 1141-1146	1.8	28
371	Dominant recombination center in electron-irradiated 3C SiC. <i>Journal of Applied Physics</i> , <b>1996</b> , 79, 3784-3786		28
370	Spin injection and helicity control of surface spin photocurrent in a three dimensional topological insulator. <i>Nature Communications</i> , <b>2017</b> , 8, 15401	17.4	27
369	Suppression of non-radiative surface recombination by N incorporation in GaAs/GaNAs core/shell nanowires. <i>Scientific Reports</i> , <b>2015</b> , 5, 11653	4.9	27
368	Mechanism for radiative recombination and defect properties of GaP/GaNP core/shell nanowires. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 163106	3.4	27
367	Origin of n-type conductivity of low-temperature grown InP. <i>Journal of Applied Physics</i> , <b>1994</b> , 76, 600-602	2.5	27
366	Long lifetime of free excitons in ZnO tetrapod structures. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 083104	3.4	26
365	Defects in dilute nitrides. <i>Journal of Physics Condensed Matter</i> , <b>2004</b> , 16, S3027-S3035	1.8	26

364	Optical characterization of III-nitrides. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2002</b> , 93, 112-122	3.1	26
363	Transfer processes for excitons bound to complex defects in GaP studied by optical detection of magnetic resonance. <i>Physical Review B</i> , <b>1988</b> , 37, 2570-2577	3.3	26
362	Magnetizing lead-free halide double perovskites. <i>Science Advances</i> , <b>2020</b> , 6,	14.3	25
361	Electron spin filtering by thin GaNAs/GaAs multiquantum wells. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 052104	3.4	25
360	Mechanism for thermal quenching of luminescence in SiGe/Si structures grown by molecular beam epitaxy: Role of nonradiative defects. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 3676-3678	3.4	25
359	Experimental evidence for N-induced strong coupling of host conduction band states in GaN <sub>x</sub> P <sub>1-x</sub> : Insight into the dominant mechanism for giant band-gap bowing. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	25
358	Identification of a dominant mechanism for optical spin injection from a diluted magnetic semiconductor: Spin-conserving energy transfer via localized excitations. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	25
357	Possible lifetime-limiting defect in 6H SiC. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 2687-2689	3.4	25
356	Role of free carriers in the application of optically detected magnetic resonance for studies of defects in silicon. <i>Applied Physics A: Solids and Surfaces</i> , <b>1991</b> , 53, 130-135		25
355	Spectroelectrochemistry and Nature of Charge Carriers in Self-Doped Conducting Polymer. <i>Advanced Electronic Materials</i> , <b>2017</b> , 3, 1700096	6.4	25
354	Origin of radiative recombination and manifestations of localization effects in GaAs/GaNAs core/shell nanowires. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 253106	3.4	24
353	SiC as semiconductor for high-power, high-temperature and high-frequency devices. <i>Physica Scripta</i> , <b>1994</b> , T54, 283-290	2.6	24
352	Mechanism for radiative recombination in ZnCdO alloys. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 261907	3.4	23
351	Efficient spin depolarization in ZnCdSe spin detector: an important factor limiting optical spin injection efficiency in ZnMnSe <sub>z</sub> /ZnCdSe spin light-emitting structures. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 5260-5262	3.4	23
350	Structural properties of a GaN <sub>x</sub> P <sub>1-x</sub> alloy: Raman studies. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 3959-3961	3.4	23
349	Energy upconversion in GaP/GaNP core/shell nanowires for enhanced near-infrared light harvesting. <i>Small</i> , <b>2014</b> , 10, 4403-8	11	22
348	Dynamics of exciton-spin injection, transfer, and relaxation in self-assembled quantum dots of CdSe coupled with a diluted magnetic semiconductor layer of Zn <sub>0.80</sub> Mn <sub>0.20</sub> Se. <i>Physical Review B</i> , <b>2007</b> , 75,	3.3	22
347	Zero-field optical detection of magnetic resonance on a metastable sulfur-pair-related defect in silicon: Evidence for a Cu constituent. <i>Physical Review B</i> , <b>1992</b> , 46, 12316-12322	3.3	22

346	Enhancement of polymer endurance to UV light by incorporation of semiconductor nanoparticles. <i>Nanoscale Research Letters</i> , <b>2015</b> , 10, 81	5	21
345	Room-temperature electron spin amplifier based on Ga(In)NAs alloys. <i>Advanced Materials</i> , <b>2013</b> , 25, 738-42		21
344	Efficient upconversion of photoluminescence via two-photon absorption in bulk and nanorod ZnO. <i>Applied Physics B: Lasers and Optics</i> , <b>2012</b> , 108, 919-924	1.9	21
343	Effects of hydrogen on the optical properties of ZnCdO/ZnO quantum wells grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 261912	3.4	21
342	Direct experimental evidence for unusual effects of hydrogen on the electronic and vibrational properties of GaN <sub>x</sub> P <sub>1-x</sub> alloys: A proof for a general property of dilute nitrides. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	21
341	Optically detected cyclotron resonance investigations on 4H and 6H SiC: Band-structure and transport properties. <i>Physical Review B</i> , <b>2000</b> , 61, 4844-4849	3.3	21
340	Sequential Doping of Ladder-Type Conjugated Polymers for Thermally Stable n-Type Organic Conductors. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2020</b> , 12, 53003-53011	9.5	21
339	Nonequilibrium site distribution governs charge-transfer electroluminescence at disordered organic heterointerfaces. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , <b>2019</b> , 116, 23416-23425	11.5	20
338	Effective Masses in SiC Determined by Cyclotron Resonance Experiments. <i>Physica Status Solidi A</i> , <b>1997</b> , 162, 79-93		20
337	Point defects in dilute nitride III-NAs and III-NB. <i>Physica B: Condensed Matter</i> , <b>2006</b> , 376-377, 545-551	2.8	20
336	Control of spin functionality in ZnMnSe-based structures: Spin switching versus spin alignment. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 1700-1702	3.4	20
335	Strongly polarized quantum-dot-like light emitters embedded in GaAs/GaNAs core/shell nanowires. <i>Nanoscale</i> , <b>2016</b> , 8, 15939-47	7.7	19
334	Paramagnetic centers in detonation nanodiamonds studied by CW and pulse EPR. <i>Chemical Physics Letters</i> , <b>2010</b> , 493, 319-322	2.5	19
333	As-Grown 4H-SiC Epilayers with Magnetic Properties. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 747-750	0.4	19
332	Charge Generation via Relaxed Charge-Transfer States in Organic Photovoltaics by an Energy-Disorder-Driven Entropy Gain. <i>Journal of Physical Chemistry C</i> , <b>2018</b> , 122, 12640-12646	3.8	19
331	Raman spectroscopy of GaP/GaNP core/shell nanowires. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 193102	3.4	18
330	Identification of Ga-interstitial defects in GaN <sub>y</sub> P <sub>1-y</sub> and Al <sub>x</sub> Ga <sub>1-x</sub> N <sub>y</sub> P <sub>1-y</sub> . <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	18
329	Intrinsic Doping: A New Approach for n-Type Modulation Doping in InP-Based Heterostructures. <i>Physical Review Letters</i> , <b>1996</b> , 77, 2734-2737	7.4	18

328	PGa-antisite-related neutral complex defect in GaP studied with optically detected magnetic resonance. <i>Physical Review B</i> , <b>1987</b> , 36, 5058-5061	3.3	18
327	Near-Infrared Lasing at 1 $\mu\text{m}$ from a Dilute-Nitride-Based Multishell Nanowire. <i>Nano Letters</i> , <b>2019</b> , 19, 885-890	11.5	18
326	Impact of Singly Occupied Molecular Orbital Energy on the n-Doping Efficiency of Benzimidazole Derivatives. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 37981-37990	9.5	17
325	Origin of strong photoluminescence polarization in GaNP nanowires. <i>Nano Letters</i> , <b>2014</b> , 14, 5264-9	11.5	17
324	Efficient nitrogen incorporation in ZnO nanowires. <i>Scientific Reports</i> , <b>2015</b> , 5, 13406	4.9	17
323	Catalytic conversion of C2-C3 alcohols on detonation nanodiamond and its modifications. <i>Russian Journal of Physical Chemistry A</i> , <b>2012</b> , 86, 26-31	0.7	17
322	Dominant factors limiting efficiency of optical spin detection in ZnO-based materials. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 092103	3.4	17
321	Effects of stoichiometry on defect formation in ZnO epilayers grown by molecular-beam epitaxy: An optically detected magnetic resonance study. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 023712	2.5	17
320	Efficient spin relaxation in InGa <sub>0.5</sub> GaN and InGa <sub>0.5</sub> GaMnN quantum wells: An obstacle to spin detection. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 192107	3.4	17
319	Photoluminescence of the two-dimensional hole gas in p-type delta -doped Si layers. <i>Physical Review B</i> , <b>1996</b> , 53, 9587-9590	3.3	17
318	Steady-state level-anticrossing spectra for bound-exciton triplets associated with complex defects in semiconductors. <i>Physical Review B</i> , <b>1990</b> , 41, 5746-5755	3.3	17
317	Near-Infrared Light-Responsive Cu-Doped Cs <sub>2</sub> AgBiBr <sub>6</sub> . <i>Advanced Functional Materials</i> , <b>2020</b> , 30, 2005521	15.6	17
316	Effects of Polytypism on Optical Properties and Band Structure of Individual Ga(N)P Nanowires from Correlative Spatially Resolved Structural and Optical Studies. <i>Nano Letters</i> , <b>2015</b> , 15, 4052-8	11.5	16
315	Identification of an isolated arsenic antisite defect in GaAsBi. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 052110	3.4	16
314	Optical investigation of Fermi-edge singularities in Al <sub>0.35</sub> Ga <sub>0.65</sub> As/GaAs heterostructures. <i>Physical Review B</i> , <b>1992</b> , 46, 4352-4355	3.3	16
313	Optical properties and excitation-induced distortions of a trigonal Cu-related neutral complex with a bound exciton at 2.26 eV in ZnTe. <i>Physical Review B</i> , <b>1986</b> , 34, 8656-8666	3.3	16
312	Optically detected magnetic resonance investigation of a deep Li-related complex in GaP. <i>Physical Review B</i> , <b>1985</b> , 32, 6650-6654	3.3	16
311	Optimizing GaNP coaxial nanowires for efficient light emission by controlling formation of surface and interfacial defects. <i>Nano Letters</i> , <b>2015</b> , 15, 242-7	11.5	15



310	Effects of Ni-coating on ZnO nanowires: A Raman scattering study. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 214302	2.5	15
309	Defect properties of ZnO nanowires revealed from an optically detected magnetic resonance study. <i>Nanotechnology</i> , <b>2013</b> , 24, 015701	3.4	15
308	Similarity between the 0.88-eV photoluminescence in GaN and the electron-capture emission of the OP donor in GaP. <i>Physical Review B</i> , <b>1998</b> , 58, R13351-R13354	3.3	15
307	Electronic properties of low-temperature InP. <i>Journal of Electronic Materials</i> , <b>1993</b> , 22, 1487-1490	1.9	15
306	Optically detected magnetic resonance studies of low-temperature InP. <i>Journal of Electronic Materials</i> , <b>1993</b> , 22, 1491-1494	1.9	15
305	Effect of Side Groups on the Photovoltaic Performance Based on Porphyrin-Perylene Bisimide Electron Acceptors. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 32454-32461	9.5	15
304	Interfacial bonding in a CdS/PVA nanocomposite: A Raman scattering study. <i>Journal of Colloid and Interface Science</i> , <b>2015</b> , 452, 33-37	9.3	14
303	Dynamics of donor bound excitons in ZnO. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 121103	3.4	14
302	Strong room-temperature optical and spin polarization in InAs/GaAs quantum dot structures. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 203110	3.4	14
301	Formation of grown-in defects in molecular beam epitaxial Ga(In)NP: Effects of growth conditions and postgrowth treatments. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 063519	2.5	14
300	Efficiency of optical spin injection and spin loss from a diluted magnetic semiconductor ZnMnSe to CdSe nonmagnetic quantum dots. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	14
299	Optical study of spin injection dynamics in InGaN/GaN quantum wells with GaMnN injection layers. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2004</b> , 22, 2668		14
298	Formation of Ga interstitials in (Al,In) <sub>y</sub> Ga <sub>1-y</sub> N <sub>x</sub> P <sub>1-x</sub> alloys and their role in carrier recombination. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 2827-2829	3.4	14
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